

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-GSM850-251CH****DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1; Serial: SAR1**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface),  $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 67.58 V/m; Power Drift = 0.05 dB

PMF = 2.830 is applied.

E-field emissions = 150.9 V/m

**Near-field category: M3 (AWF -5 dB)**

PMF scaled E-field

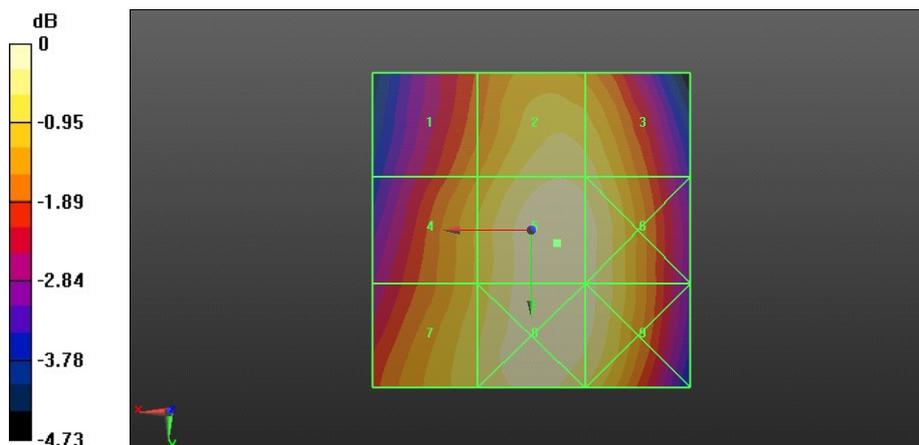
Grid 1 M4 130.2 V/m	Grid 2 M4 145.3 V/m	Grid 3 M4 143.3 V/m
Grid 4 M4 136.5 V/m	Grid 5 M3 150.9 V/m	Grid 6 M4 148.3 V/m
Grid 7 M4 140.4 V/m	Grid 8 M3 150.7 V/m	Grid 9 M4 148.1 V/m

**Cursor:**

Total = 150.9 V/m

E Category: M3

Location: -4, 2, 8.7 mm



0 dB = 150.9 V/m = 43.57 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-GSM850-190CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1; Serial: SAR1**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz; Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 69.89 V/m; Power Drift = 0.04 dB

PMF = 2.830 is applied.

E-field emissions = 156.8 V/m

**Near-field category: M3 (AWF -5 dB)**

PMF scaled E-field

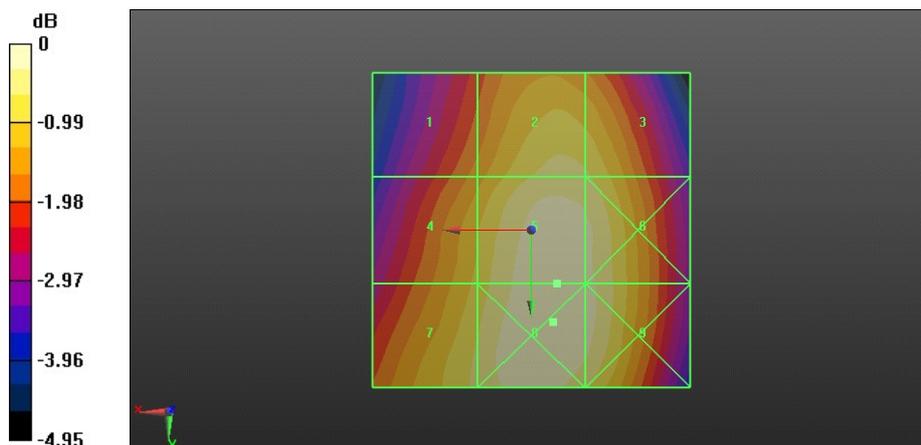
Grid 1 M4 133.0 V/m	Grid 2 M4 148.9 V/m	Grid 3 M4 147.1 V/m
Grid 4 M4 142.2 V/m	Grid 5 M3 156.8 V/m	Grid 6 M3 153.9 V/m
Grid 7 M4 147.4 V/m	Grid 8 M3 157.4 V/m	Grid 9 M3 154.2 V/m

**Cursor:**

Total = 157.4 V/m

E Category: M3

Location: -3.5, 14.5, 8.7 mm



0 dB = 157.4 V/m = 43.94 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-GSM850-128CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1; Serial: SAR1**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz; Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 65.22 V/m; Power Drift = -0.07 dB

PMF = 2.830 is applied.

E-field emissions = 144.0 V/m

**Near-field category: M4 (AWF -5 dB)**

PMF scaled E-field

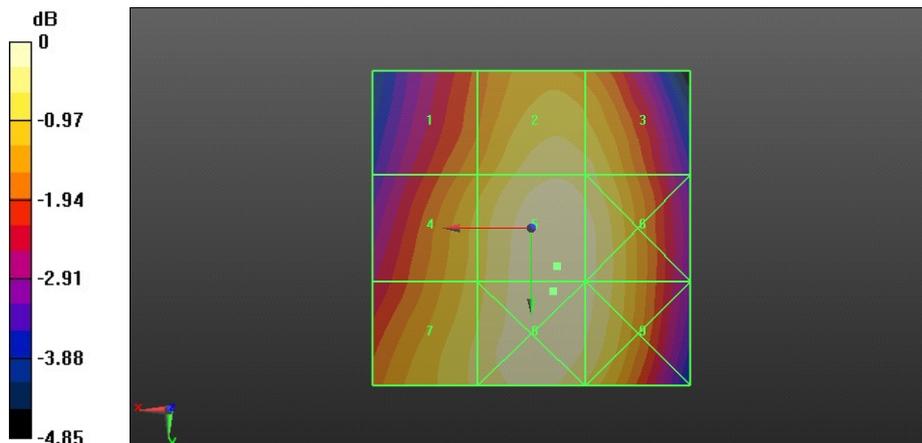
Grid 1 M4 124.7 V/m	Grid 2 M4 138.3 V/m	Grid 3 M4 136.2 V/m
Grid 4 M4 131.9 V/m	Grid 5 M4 144.0 V/m	Grid 6 M4 141.3 V/m
Grid 7 M4 135.3 V/m	Grid 8 M4 144.0 V/m	Grid 9 M4 141.1 V/m

**Cursor:**

Total = 144.0 V/m

E Category: M4

Location: -3.5, 10, 8.7 mm



0 dB = 144.0 V/m = 43.17 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-GSM850-190CH with battery 2#**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SARI**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz;Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 68.64 V/m; Power Drift = 0.01 dB

PMF = 2.830 is applied.

E-field emissions = 154.2 V/m

**Near-field category: M3 (AWF -5 dB)**

PMF scaled E-field

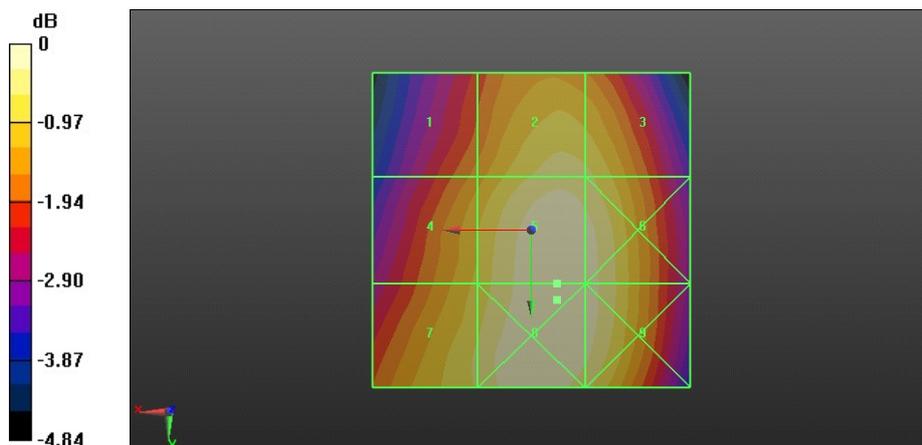
Grid 1 M4 130.9 V/m	Grid 2 M4 147.0 V/m	Grid 3 M4 145.1 V/m
Grid 4 M4 139.9 V/m	Grid 5 M3 154.2 V/m	Grid 6 M3 151.9 V/m
Grid 7 M4 144.7 V/m	Grid 8 M3 154.5 V/m	Grid 9 M3 152.0 V/m

**Cursor:**

Total = 154.5 V/m

E Category: M3

Location: -4, 11, 8.7 mm



0 dB = 154.5 V/m = 43.78 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-GSM850-251CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SARI**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06800 A/m; Power Drift = -0.02 dB

PMF = 2.820 is applied.

H-field emissions = 0.2452 A/m

**Near-field category: M4 (AWF -5 dB)**

PMF scaled H-field

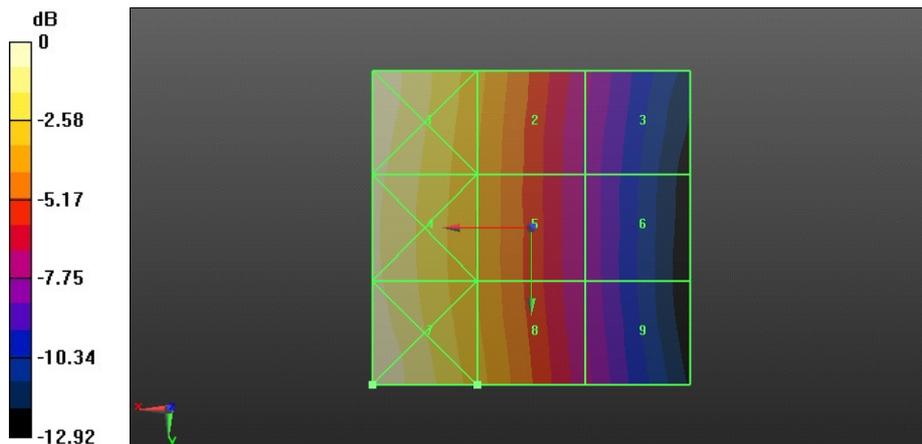
<b>Grid 1 M4</b> <b>0.342 A/m</b>	<b>Grid 2 M4</b> <b>0.243 A/m</b>	<b>Grid 3 M4</b> <b>0.147 A/m</b>
<b>Grid 4 M4</b> <b>0.327 A/m</b>	<b>Grid 5 M4</b> <b>0.235 A/m</b>	<b>Grid 6 M4</b> <b>0.141 A/m</b>
<b>Grid 7 M4</b> <b>0.348 A/m</b>	<b>Grid 8 M4</b> <b>0.245 A/m</b>	<b>Grid 9 M4</b> <b>0.148 A/m</b>

**Cursor:**

Total = 0.3480 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.3480 A/m = -9.17 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-GSM850-190CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1; Serial: SARI**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz; Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06700 A/m; Power Drift = 0.04 dB

PMF = 2.820 is applied.

H-field emissions = 0.2458 A/m

**Near-field category: M4 (AWF -5 dB)**

PMF scaled H-field

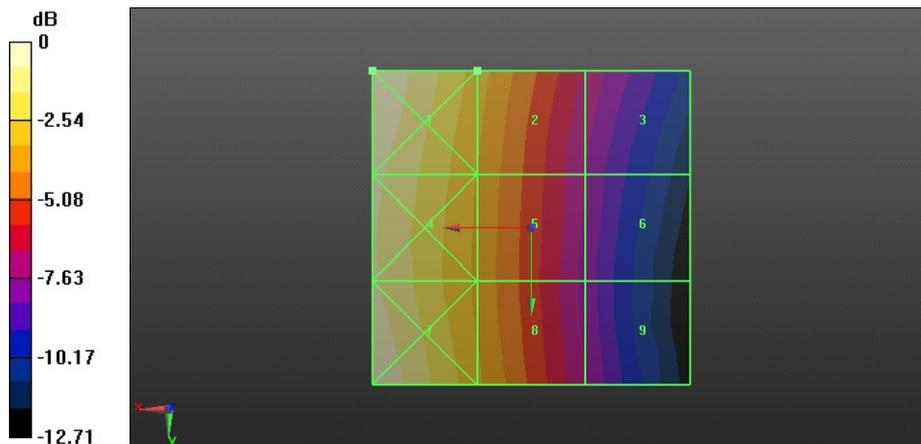
<b>Grid 1 M4</b> <b>0.344 A/m</b>	<b>Grid 2 M4</b> <b>0.246 A/m</b>	<b>Grid 3 M4</b> <b>0.155 A/m</b>
<b>Grid 4 M4</b> <b>0.321 A/m</b>	<b>Grid 5 M4</b> <b>0.233 A/m</b>	<b>Grid 6 M4</b> <b>0.143 A/m</b>
<b>Grid 7 M4</b> <b>0.339 A/m</b>	<b>Grid 8 M4</b> <b>0.239 A/m</b>	<b>Grid 9 M4</b> <b>0.144 A/m</b>

**Cursor:**

Total = 0.3439 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.3439 A/m = -9.27 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-GSM850-128CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1; Serial: SARI**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz; Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06300 A/m; Power Drift = -0.03 dB

PMF = 2.820 is applied.

H-field emissions = 0.2283 A/m

**Near-field category: M4 (AWF -5 dB)**

PMF scaled H-field

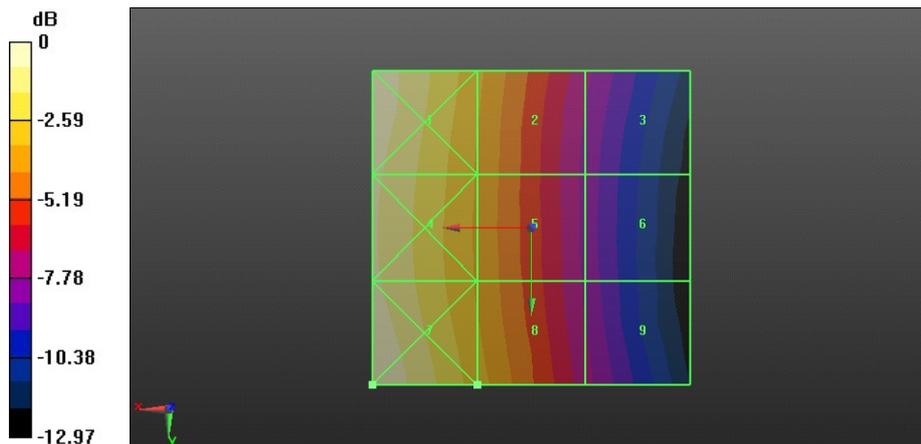
Grid 1 M4 <b>0.316 A/m</b>	Grid 2 M4 <b>0.224 A/m</b>	Grid 3 M4 <b>0.136 A/m</b>
Grid 4 M4 <b>0.301 A/m</b>	Grid 5 M4 <b>0.215 A/m</b>	Grid 6 M4 <b>0.130 A/m</b>
Grid 7 M4 <b>0.324 A/m</b>	Grid 8 M4 <b>0.228 A/m</b>	Grid 9 M4 <b>0.138 A/m</b>

**Cursor:**

Total = 0.3236 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.3236 A/m = -9.80 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-GSM850-190CH with battery 2#**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SAR1**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz;Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06700 A/m; Power Drift = -0.09 dB

PMF = 2.820 is applied.

H-field emissions = 0.2431 A/m

**Near-field category: M4 (AWF -5 dB)**

PMF scaled H-field

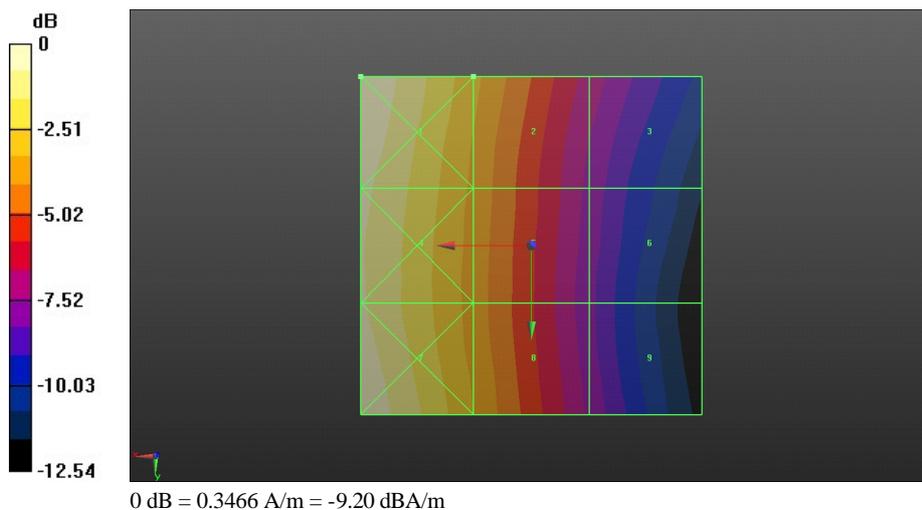
Grid 1 M4 0.347 A/m	Grid 2 M4 0.243 A/m	Grid 3 M4 0.155 A/m
Grid 4 M4 0.323 A/m	Grid 5 M4 0.231 A/m	Grid 6 M4 0.142 A/m
Grid 7 M4 0.342 A/m	Grid 8 M4 0.236 A/m	Grid 9 M4 0.144 A/m

**Cursor:**

Total = 0.3466 A/m

H Category: M4

Location: 25, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-GSM1900-810CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1; Serial: SAR1**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 10.34 V/m; Power Drift = 0.12 dB

PMF = 2.860 is applied.

E-field emissions = 47.62 V/m

**Near-field category: M3 (AWF -5 dB)**

PMF scaled E-field

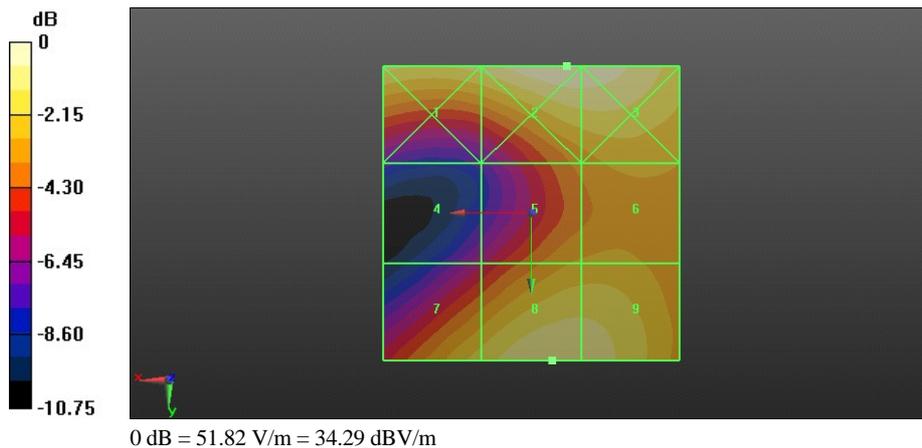
Grid 1 M4 45.89 V/m	Grid 2 M3 51.82 V/m	Grid 3 M3 51.62 V/m
Grid 4 M4 26.27 V/m	Grid 5 M4 37.94 V/m	Grid 6 M4 38.54 V/m
Grid 7 M4 42.41 V/m	Grid 8 M3 47.62 V/m	Grid 9 M4 46.31 V/m

**Cursor:**

Total = 51.82 V/m

E Category: M3

Location: -6, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-GSM1900-661CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1; Serial: SAR1**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz; Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 10.14 V/m; Power Drift = 0.09 dB

PMF = 2.860 is applied.

E-field emissions = 48.21 V/m

**Near-field category: M3 (AWF -5 dB)**

PMF scaled E-field

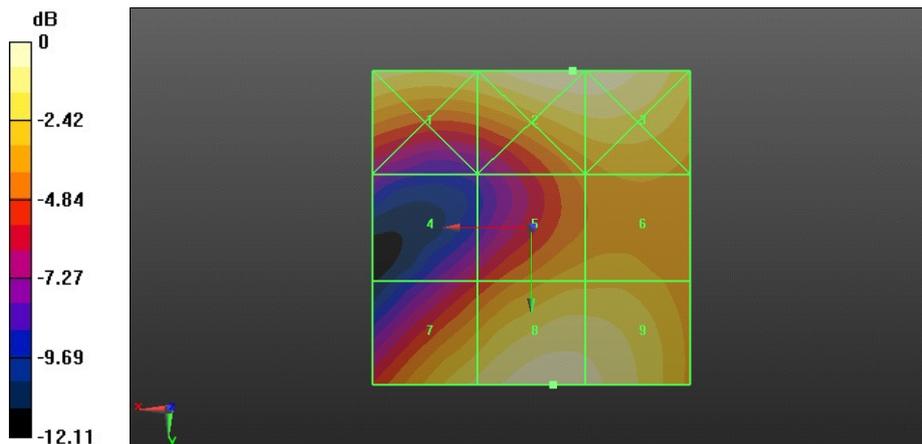
Grid 1 M4 44.41 V/m	Grid 2 M3 49.85 V/m	Grid 3 M3 49.72 V/m
Grid 4 M4 25.72 V/m	Grid 5 M4 36.84 V/m	Grid 6 M4 37.11 V/m
Grid 7 M4 42.73 V/m	Grid 8 M3 48.21 V/m	Grid 9 M4 46.88 V/m

**Cursor:**

Total = 49.85 V/m

E Category: M3

Location: -6.5, -25, 8.7 mm



0 dB = 49.85 V/m = 33.95 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-GSM1900-512CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1; Serial: SAR1**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz; Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 11.04 V/m; Power Drift = 0.07 dB

PMF = 2.860 is applied.

E-field emissions = 47.66 V/m

**Near-field category: M3 (AWF -5 dB)**

PMF scaled E-field

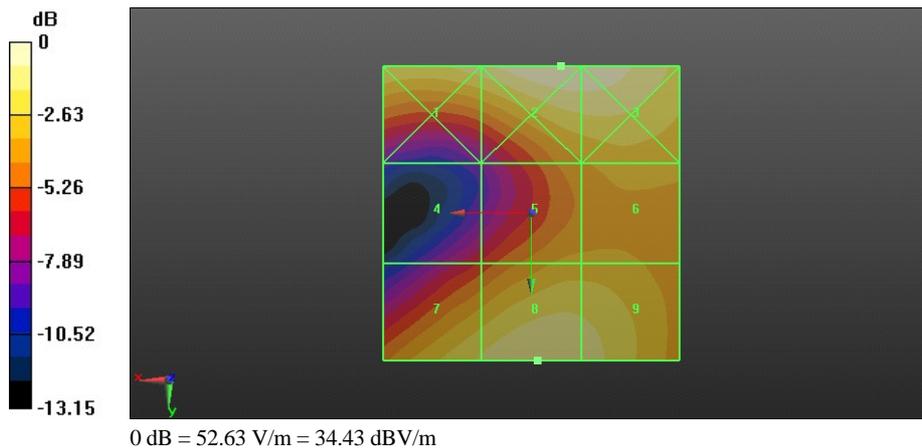
Grid 1 M4 46.19 V/m	Grid 2 M3 52.63 V/m	Grid 3 M3 52.22 V/m
Grid 4 M4 26.60 V/m	Grid 5 M4 36.67 V/m	Grid 6 M4 37.19 V/m
Grid 7 M4 43.81 V/m	Grid 8 M3 47.66 V/m	Grid 9 M4 45.50 V/m

**Cursor:**

Total = 52.63 V/m

E Category: M3

Location: -5, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-GSM1900-661CH with battery 2#****DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SAR1**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 9.315 V/m; Power Drift = 0.01 dB

PMF = 2.860 is applied.

E-field emissions = 45.87 V/m

**Near-field category: M4 (AWF -5 dB)**

PMF scaled E-field

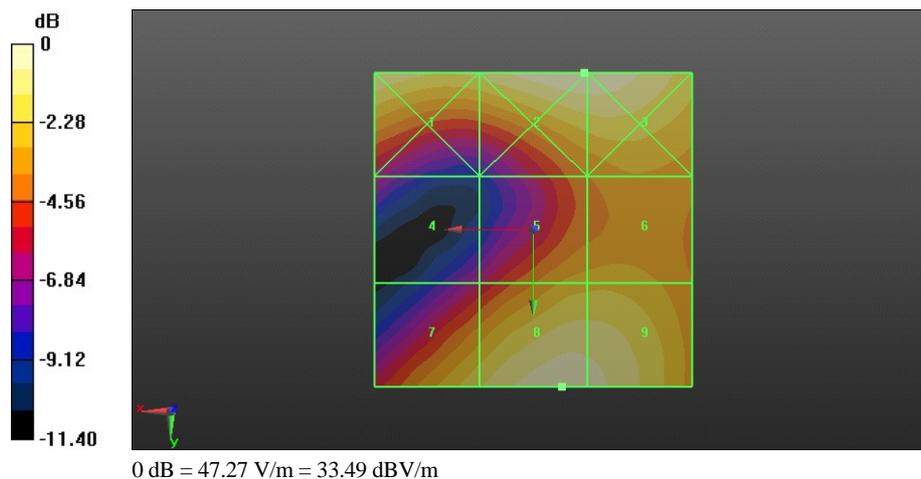
Grid 1 M4 44.11 V/m	Grid 2 M4 47.27 V/m	Grid 3 M4 47.24 V/m
Grid 4 M4 23.19 V/m	Grid 5 M4 35.23 V/m	Grid 6 M4 35.57 V/m
Grid 7 M4 39.51 V/m	Grid 8 M4 45.87 V/m	Grid 9 M4 44.88 V/m

**Cursor:**

Total = 47.27 V/m

E Category: M4

Location: -8, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-GSM1900-810CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SARI**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05200 A/m; Power Drift = 0.00 dB

PMF = 2.830 is applied.

H-field emissions = 0.1412 A/m

**Near-field category: M3 (AWF -5 dB)**

PMF scaled H-field

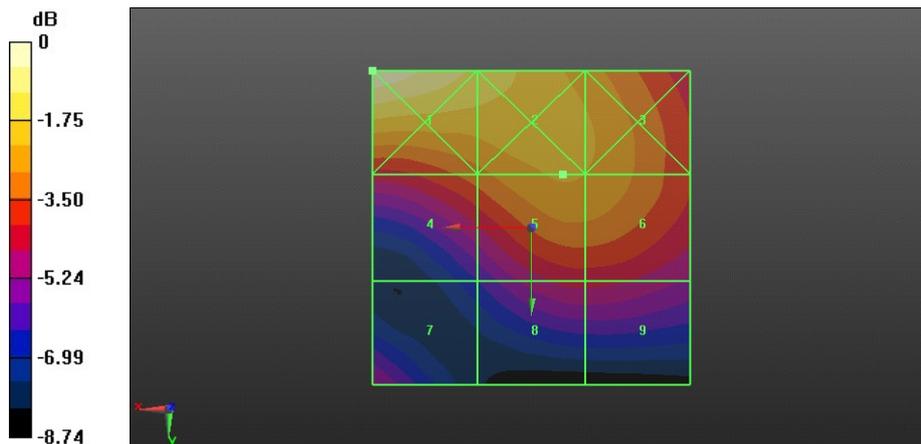
Grid 1 <b>M3</b> <b>0.183 A/m</b>	Grid 2 <b>M3</b> <b>0.158 A/m</b>	Grid 3 <b>M3</b> <b>0.142 A/m</b>
Grid 4 <b>M4</b> <b>0.128 A/m</b>	Grid 5 <b>M3</b> <b>0.141 A/m</b>	Grid 6 <b>M4</b> <b>0.140 A/m</b>
Grid 7 <b>M4</b> <b>0.104 A/m</b>	Grid 8 <b>M4</b> <b>0.110 A/m</b>	Grid 9 <b>M4</b> <b>0.110 A/m</b>

**Cursor:**

Total = 0.1831 A/m

H Category: M3

Location: 25, -25, 8.7 mm



0 dB = 0.1831 A/m = -14.75 dB(A/m)

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-GSM1900-661CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SAR1**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05300 A/m; Power Drift = 0.00 dB

PMF = 2.830 is applied.

H-field emissions = 0.1402 A/m

**Near-field category: M3 (AWF -5 dB)**

PMF scaled H-field

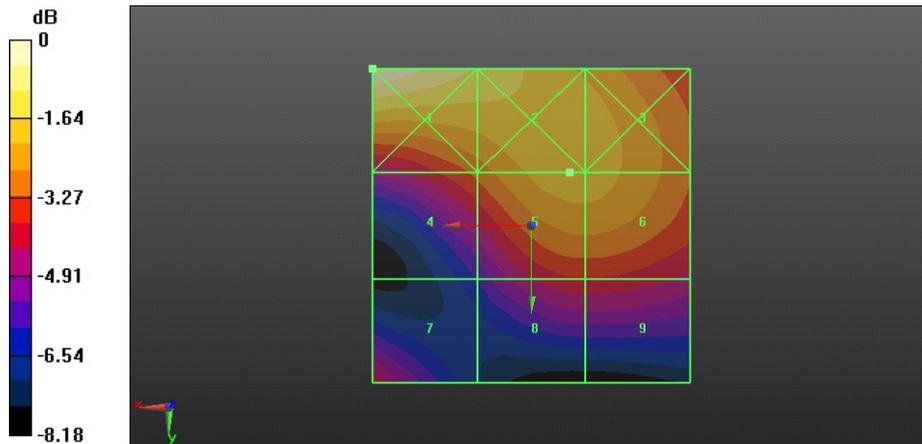
Grid 1 <b>M3</b> <b>0.174 A/m</b>	Grid 2 <b>M3</b> <b>0.153 A/m</b>	Grid 3 <b>M3</b> <b>0.141 A/m</b>
Grid 4 <b>M4</b> <b>0.122 A/m</b>	Grid 5 <b>M3</b> <b>0.140 A/m</b>	Grid 6 <b>M4</b> <b>0.139 A/m</b>
Grid 7 <b>M4</b> <b>0.110 A/m</b>	Grid 8 <b>M4</b> <b>0.112 A/m</b>	Grid 9 <b>M4</b> <b>0.111 A/m</b>

**Cursor:**

Total = 0.1740 A/m

H Category: M3

Location: 25, -25, 8.7 mm



0 dB = 0.1740 A/m = -15.19 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-GSM1900-512CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SARI**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05600 A/m; Power Drift = -0.02 dB

PMF = 2.830 is applied.

H-field emissions = 0.1435 A/m

**Near-field category: M3 (AWF -5 dB)**

PMF scaled H-field

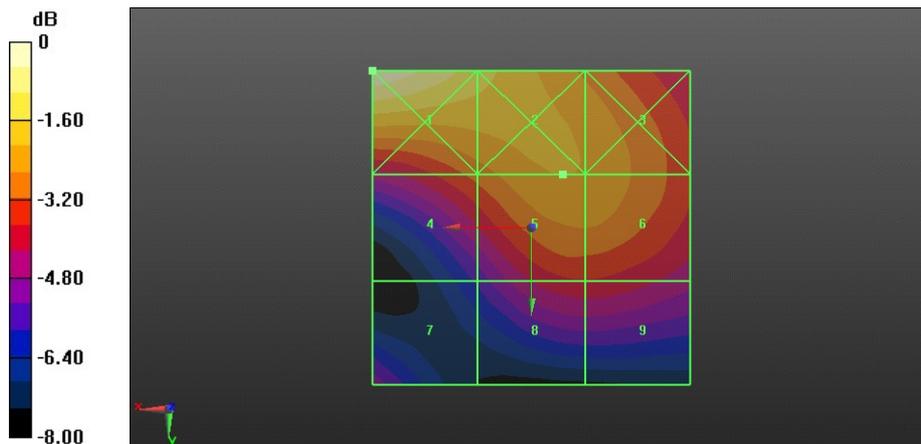
Grid 1 <b>M3</b> <b>0.183 A/m</b>	Grid 2 <b>M3</b> <b>0.157 A/m</b>	Grid 3 <b>M3</b> <b>0.143 A/m</b>
Grid 4 <b>M4</b> <b>0.130 A/m</b>	Grid 5 <b>M3</b> <b>0.143 A/m</b>	Grid 6 <b>M3</b> <b>0.143 A/m</b>
Grid 7 <b>M4</b> <b>0.105 A/m</b>	Grid 8 <b>M4</b> <b>0.119 A/m</b>	Grid 9 <b>M4</b> <b>0.119 A/m</b>

**Cursor:**

Total = 0.1831 A/m

H Category: M3

Location: 25, -25, 8.7 mm



0 dB = 0.1831 A/m = -14.74 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-GSM1900-512CH with battery 2#**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SARI**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05400 A/m; Power Drift = 0.07 dB

PMF = 2.830 is applied.

H-field emissions = 0.1412 A/m

**Near-field category: M3 (AWF -5 dB)**

PMF scaled H-field

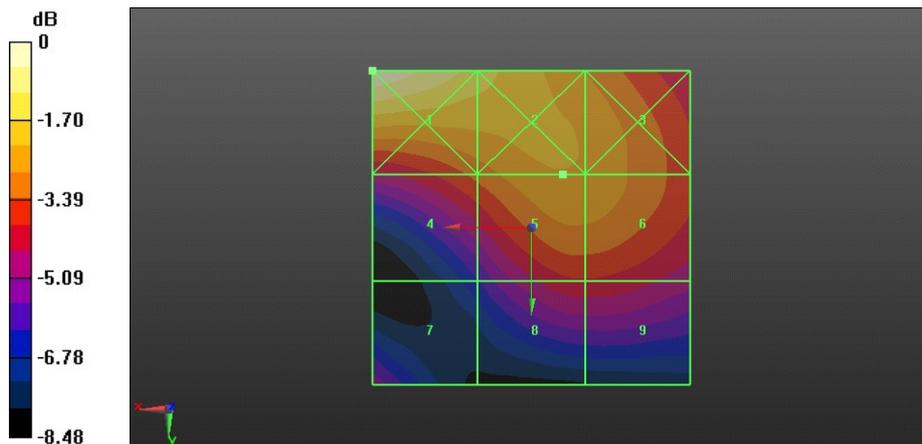
Grid 1 <b>M3</b> <b>0.184 A/m</b>	Grid 2 <b>M3</b> <b>0.157 A/m</b>	Grid 3 <b>M3</b> <b>0.141 A/m</b>
Grid 4 <b>M4</b> <b>0.127 A/m</b>	Grid 5 <b>M3</b> <b>0.141 A/m</b>	Grid 6 <b>M3</b> <b>0.140 A/m</b>
Grid 7 <b>M4</b> <b>0.101 A/m</b>	Grid 8 <b>M4</b> <b>0.116 A/m</b>	Grid 9 <b>M4</b> <b>0.116 A/m</b>

**Cursor:**

Total = 0.1836 A/m

H Category: M3

Location: 25, -25, 8.7 mm



0 dB = 0.1836 A/m = -14.72 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-UMTS Band II-9538CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SAR1**

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 12.05 V/m; Power Drift = -0.05 dB

PMF = 1.020 is applied.

E-field emissions = 21.45 V/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled E-field

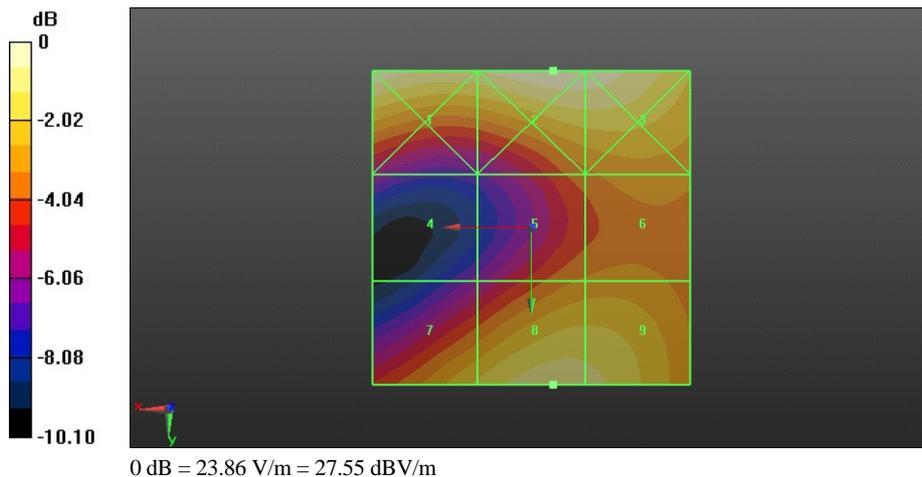
<b>Grid 1 M4</b> <b>23.81 V/m</b>	<b>Grid 2 M4</b> <b>23.86 V/m</b>	<b>Grid 3 M4</b> <b>23.54 V/m</b>
<b>Grid 4 M4</b> <b>12.12 V/m</b>	<b>Grid 5 M4</b> <b>16.50 V/m</b>	<b>Grid 6 M4</b> <b>16.96 V/m</b>
<b>Grid 7 M4</b> <b>19.32 V/m</b>	<b>Grid 8 M4</b> <b>21.45 V/m</b>	<b>Grid 9 M4</b> <b>21.07 V/m</b>

**Cursor:**

Total = 23.86 V/m

E Category: M4

Location: -3.5, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-UMTS Band II-9400CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SAR1**

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 13.36 V/m; Power Drift = -0.03 dB

PMF = 1.020 is applied.

E-field emissions = 22.90 V/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled E-field

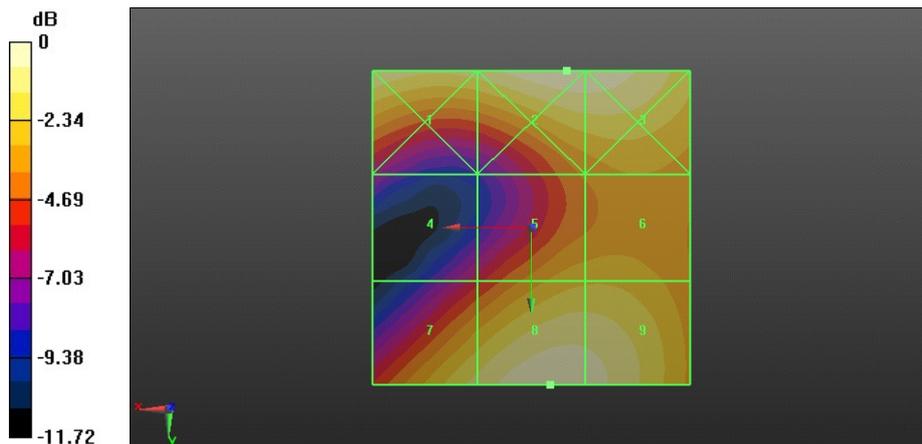
Grid 1 M4 21.65 V/m	Grid 2 M4 23.30 V/m	Grid 3 M4 23.17 V/m
Grid 4 M4 12.06 V/m	Grid 5 M4 17.54 V/m	Grid 6 M4 17.63 V/m
Grid 7 M4 20.27 V/m	Grid 8 M4 22.90 V/m	Grid 9 M4 22.27 V/m

**Cursor:**

Total = 23.30 V/m

E Category: M4

Location: -5.5, -25, 8.7 mm



0 dB = 23.30 V/m = 27.35 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-UMTS Band II-9262CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1; Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 14.71 V/m; Power Drift = -0.02 dB

PMF = 1.020 is applied.

E-field emissions = 22.79 V/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled E-field

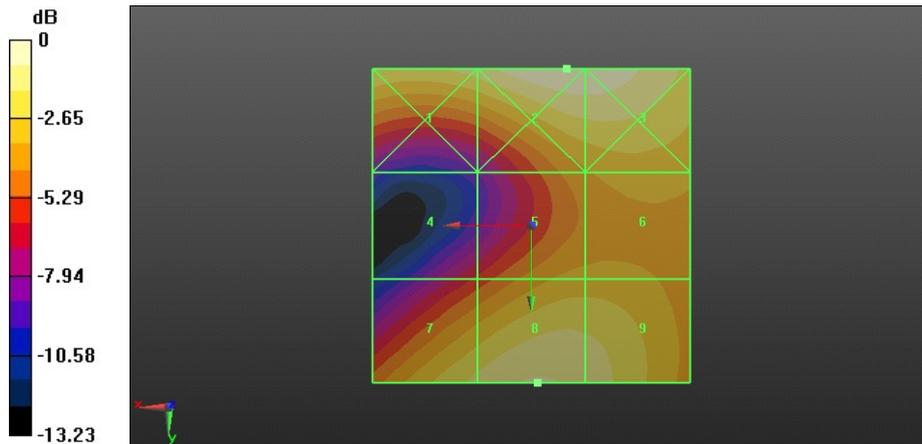
Grid 1 M4 <b>21.70 V/m</b>	Grid 2 M4 <b>24.98 V/m</b>	Grid 3 M4 <b>24.83 V/m</b>
Grid 4 M4 <b>12.67 V/m</b>	Grid 5 M4 <b>17.45 V/m</b>	Grid 6 M4 <b>17.60 V/m</b>
Grid 7 M4 <b>21.06 V/m</b>	Grid 8 M4 <b>22.79 V/m</b>	Grid 9 M4 <b>21.72 V/m</b>

**Cursor:**

Total = 24.98 V/m

E Category: M4

Location: -5.5, -25, 8.7 mm



0 dB = 24.98 V/m = 27.95 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-UMTS Band II-9400CH with battery 2#****DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SAR1**

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 12.79 V/m; Power Drift = 0.04 dB

PMF = 1.020 is applied.

E-field emissions = 22.68 V/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled E-field

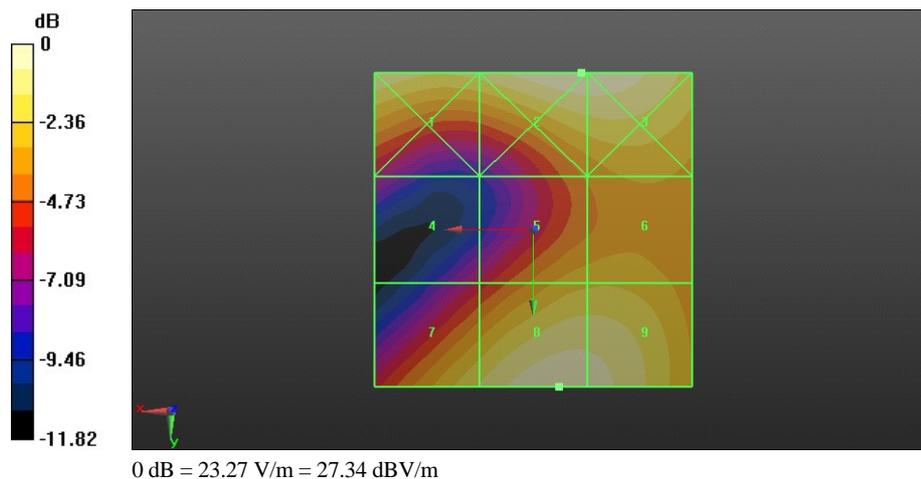
Grid 1 M4 21.60 V/m	Grid 2 M4 23.27 V/m	Grid 3 M4 23.25 V/m
Grid 4 M4 11.65 V/m	Grid 5 M4 17.41 V/m	Grid 6 M4 17.59 V/m
Grid 7 M4 19.66 V/m	Grid 8 M4 22.68 V/m	Grid 9 M4 22.25 V/m

**Cursor:**

Total = 23.27 V/m

E Category: M4

Location: -7.5, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-UMTS Band II-9538CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06500 A/m; Power Drift = -0.16 dB

PMF = 1.010 is applied.

H-field emissions = 0.06345 A/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled H-field

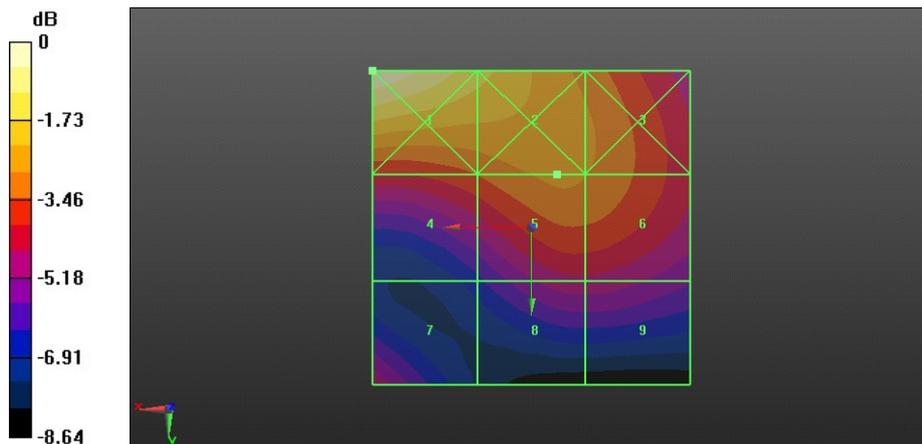
Grid 1 M4 <b>0.087 A/m</b>	Grid 2 M4 <b>0.074 A/m</b>	Grid 3 M4 <b>0.063 A/m</b>
Grid 4 M4 <b>0.059 A/m</b>	Grid 5 M4 <b>0.063 A/m</b>	Grid 6 M4 <b>0.063 A/m</b>
Grid 7 M4 <b>0.051 A/m</b>	Grid 8 M4 <b>0.050 A/m</b>	Grid 9 M4 <b>0.050 A/m</b>

**Cursor:**

Total = 0.08710 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.08710 A/m = -21.20 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-UMTS Band II-9400CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07000 A/m; Power Drift = -0.05 dB

PMF = 1.010 is applied.

H-field emissions = 0.06672 A/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled H-field

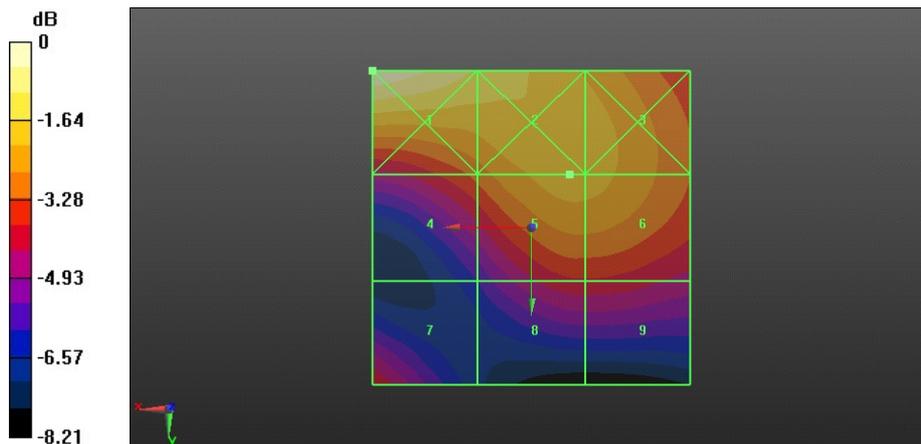
Grid 1 M4 <b>0.083 A/m</b>	Grid 2 M4 <b>0.073 A/m</b>	Grid 3 M4 <b>0.067 A/m</b>
Grid 4 M4 <b>0.058 A/m</b>	Grid 5 M4 <b>0.067 A/m</b>	Grid 6 M4 <b>0.066 A/m</b>
Grid 7 M4 <b>0.054 A/m</b>	Grid 8 M4 <b>0.053 A/m</b>	Grid 9 M4 <b>0.053 A/m</b>

**Cursor:**

Total = 0.08311 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.08311 A/m = -21.61 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-UMTS Band II-9262CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07400 A/m; Power Drift = -0.03 dB

PMF = 1.010 is applied.

H-field emissions = 0.06888 A/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled H-field

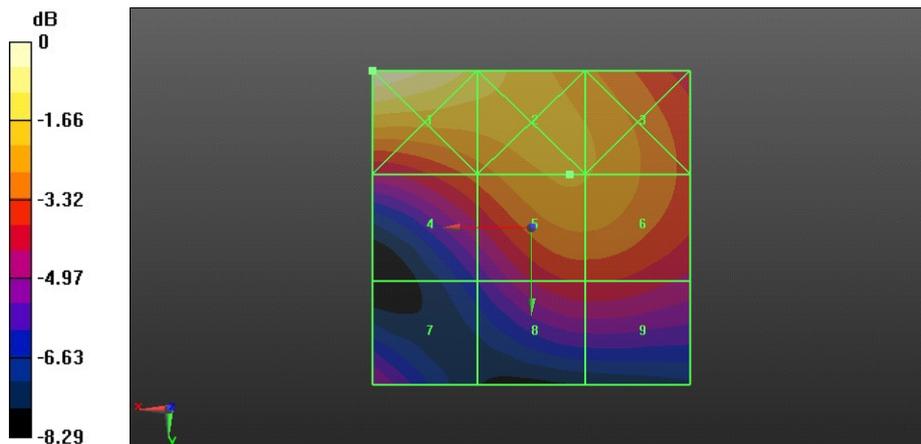
Grid 1 M4 <b>0.088 A/m</b>	Grid 2 M4 <b>0.076 A/m</b>	Grid 3 M4 <b>0.069 A/m</b>
Grid 4 M4 <b>0.062 A/m</b>	Grid 5 M4 <b>0.069 A/m</b>	Grid 6 M4 <b>0.069 A/m</b>
Grid 7 M4 <b>0.051 A/m</b>	Grid 8 M4 <b>0.057 A/m</b>	Grid 9 M4 <b>0.057 A/m</b>

**Cursor:**

Total = 0.08800 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.08800 A/m = -21.11 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-UMTS Band II-9262CH with battery 2#**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1; Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07500 A/m; Power Drift = -0.11 dB

PMF = 1.010 is applied.

H-field emissions = 0.07029 A/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled H-field

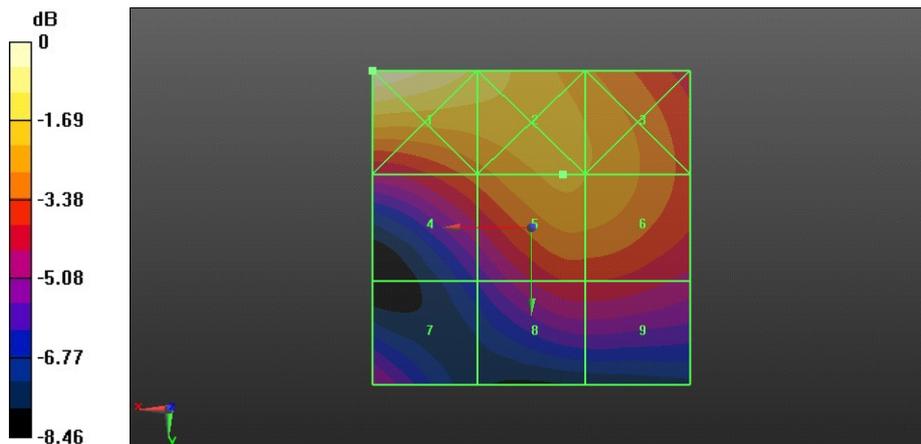
Grid 1 M4 <b>0.090 A/m</b>	Grid 2 M4 <b>0.078 A/m</b>	Grid 3 M4 <b>0.070 A/m</b>
Grid 4 M4 <b>0.063 A/m</b>	Grid 5 M4 <b>0.070 A/m</b>	Grid 6 M4 <b>0.069 A/m</b>
Grid 7 M4 <b>0.052 A/m</b>	Grid 8 M4 <b>0.057 A/m</b>	Grid 9 M4 <b>0.057 A/m</b>

**Cursor:**

Total = 0.08975 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.08975 A/m = -20.94 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-UMTS Band IV-1513CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 1752.6 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 23.03 V/m; Power Drift = -0.02 dB

PMF = 1.020 is applied.

E-field emissions = 28.30 V/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled E-field

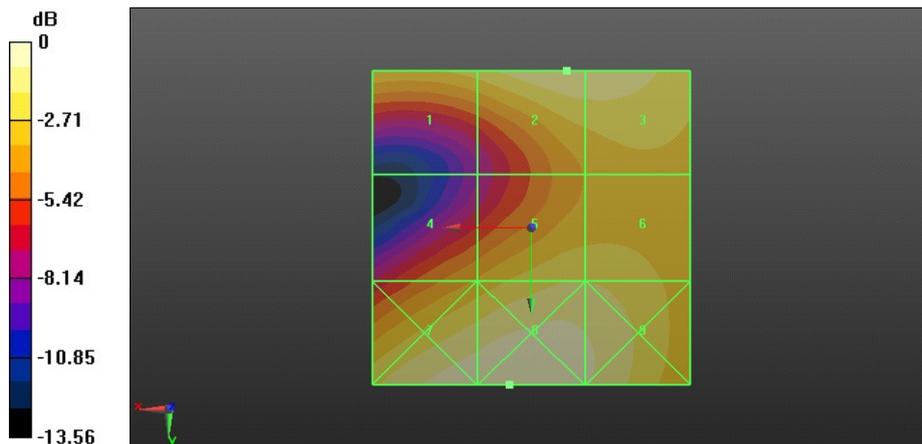
Grid 1 M4 <b>24.48 V/m</b>	Grid 2 M4 <b>28.30 V/m</b>	Grid 3 M4 <b>28.08 V/m</b>
Grid 4 M4 <b>21.07 V/m</b>	Grid 5 M4 <b>25.42 V/m</b>	Grid 6 M4 <b>25.37 V/m</b>
Grid 7 M4 <b>30.63 V/m</b>	Grid 8 M4 <b>31.31 V/m</b>	Grid 9 M4 <b>28.83 V/m</b>

**Cursor:**

Total = 31.31 V/m

E Category: M4

Location: 3.5, 25, 8.7 mm



0 dB = 31.31 V/m = 29.91 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-UMTS Band IV-1413CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1; Serial: SAR1**

Communication System: HW-UMTS-FDD; Frequency: 1732.6 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 23.41 V/m; Power Drift = 0.03 dB

PMF = 1.020 is applied.

E-field emissions = 28.49 V/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled E-field

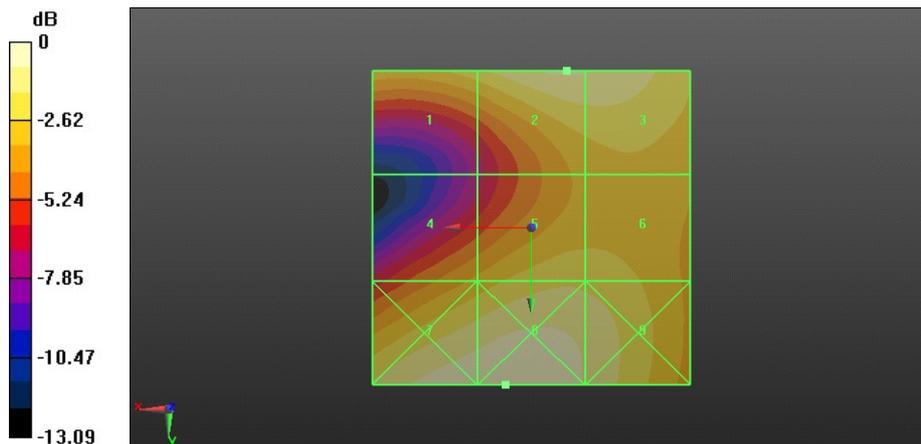
Grid 1 M4 24.64 V/m	Grid 2 M4 28.49 V/m	Grid 3 M4 28.25 V/m
Grid 4 M4 21.38 V/m	Grid 5 M4 24.90 V/m	Grid 6 M4 24.72 V/m
Grid 7 M4 30.37 V/m	Grid 8 M4 30.91 V/m	Grid 9 M4 27.78 V/m

**Cursor:**

Total = 30.91 V/m

E Category: M4

Location: 4, 25, 8.7 mm



0 dB = 30.91 V/m = 29.80 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-UMTS Band IV-1312CH****DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 24.41 V/m; Power Drift = -0.03 dB

PMF = 1.020 is applied.

E-field emissions = 28.60 V/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled E-field

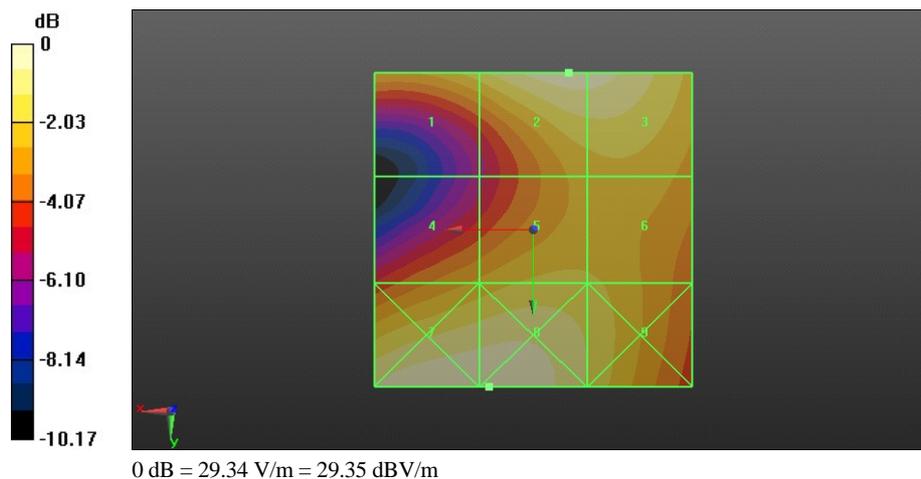
Grid 1 M4 24.59 V/m	Grid 2 M4 28.60 V/m	Grid 3 M4 28.35 V/m
Grid 4 M4 21.94 V/m	Grid 5 M4 23.90 V/m	Grid 6 M4 23.64 V/m
Grid 7 M4 29.32 V/m	Grid 8 M4 29.34 V/m	Grid 9 M4 25.06 V/m

**Cursor:**

Total = 29.34 V/m

E Category: M4

Location: 7, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-UMTS Band IV-1312CH with battery 2#****DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 23.99 V/m; Power Drift = 0.04 dB

PMF = 1.020 is applied.

E-field emissions = 28.87 V/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled E-field

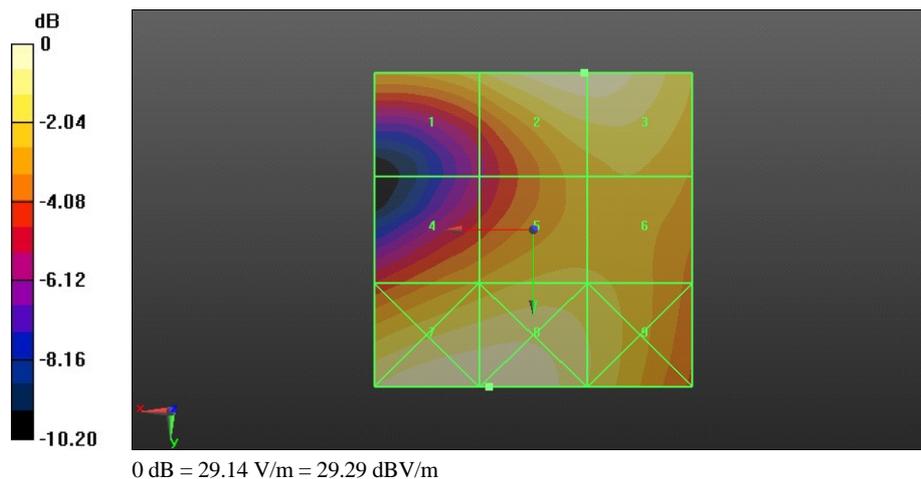
Grid 1 M4 24.61 V/m	Grid 2 M4 28.87 V/m	Grid 3 M4 28.86 V/m
Grid 4 M4 21.69 V/m	Grid 5 M4 23.75 V/m	Grid 6 M4 23.55 V/m
Grid 7 M4 29.13 V/m	Grid 8 M4 29.14 V/m	Grid 9 M4 25.15 V/m

**Cursor:**

Total = 29.14 V/m

E Category: M4

Location: 7, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-UMTS Band IV-1513CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 1752.6 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09600 A/m; Power Drift = -0.06 dB

PMF = 0.9800 is applied.

H-field emissions = 0.08745 A/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled H-field

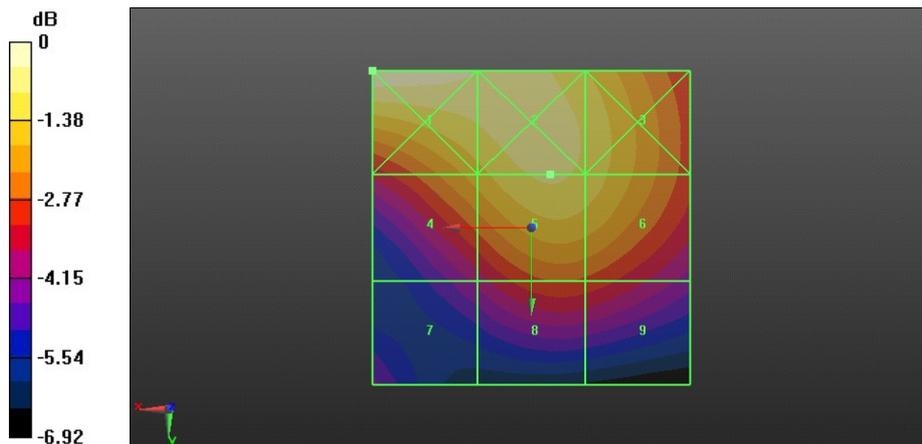
Grid 1 M4 <b>0.096 A/m</b>	Grid 2 M4 <b>0.092 A/m</b>	Grid 3 M4 <b>0.086 A/m</b>
Grid 4 M4 <b>0.080 A/m</b>	Grid 5 M4 <b>0.087 A/m</b>	Grid 6 M4 <b>0.085 A/m</b>
Grid 7 M4 <b>0.061 A/m</b>	Grid 8 M4 <b>0.070 A/m</b>	Grid 9 M4 <b>0.069 A/m</b>

**Cursor:**

Total = 0.09634 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.09634 A/m = -20.32 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-UMTS Band IV-1413CH****DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 1732.6 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface),  $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1):** Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09200 A/m; Power Drift = 0.05 dB

PMF = 0.9800 is applied.

H-field emissions = 0.08531 A/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled H-field

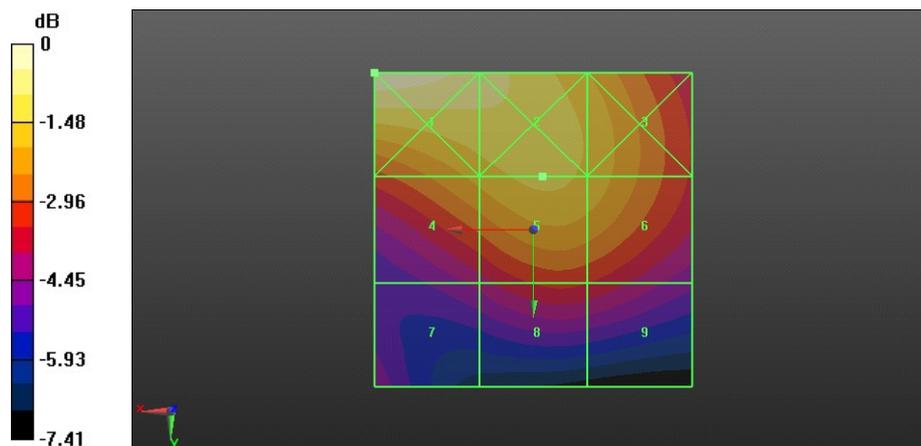
Grid 1 M4 <b>0.100 A/m</b>	Grid 2 M4 <b>0.092 A/m</b>	Grid 3 M4 <b>0.083 A/m</b>
Grid 4 M4 <b>0.081 A/m</b>	Grid 5 M4 <b>0.085 A/m</b>	Grid 6 M4 <b>0.083 A/m</b>
Grid 7 M4 <b>0.061 A/m</b>	Grid 8 M4 <b>0.068 A/m</b>	Grid 9 M4 <b>0.067 A/m</b>

**Cursor:**

Total = 0.09957 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.09957 A/m = -20.04 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-UMTS Band IV-1312CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1; Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08100 A/m; Power Drift = -0.00 dB

PMF = 0.9800 is applied.

H-field emissions = 0.07858 A/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled H-field

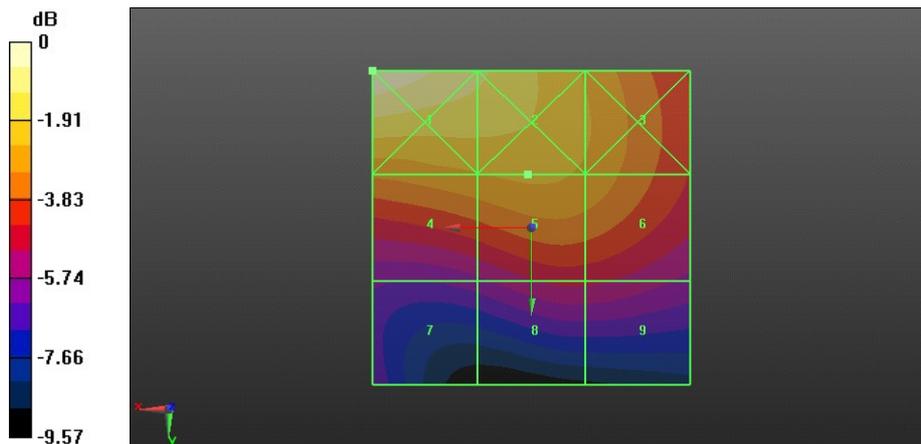
Grid 1 M4 <b>0.104 A/m</b>	Grid 2 M4 <b>0.091 A/m</b>	Grid 3 M4 <b>0.078 A/m</b>
Grid 4 M4 <b>0.077 A/m</b>	Grid 5 M4 <b>0.079 A/m</b>	Grid 6 M4 <b>0.076 A/m</b>
Grid 7 M4 <b>0.052 A/m</b>	Grid 8 M4 <b>0.059 A/m</b>	Grid 9 M4 <b>0.059 A/m</b>

**Cursor:**

Total = 0.1037 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.1037 A/m = -19.68 dB A/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-UMTS Band IV-1513CH with battery 2#**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1; Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 1752.6 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09700 A/m; Power Drift = -0.07 dB

PMF = 0.9800 is applied.

H-field emissions = 0.08832 A/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled H-field

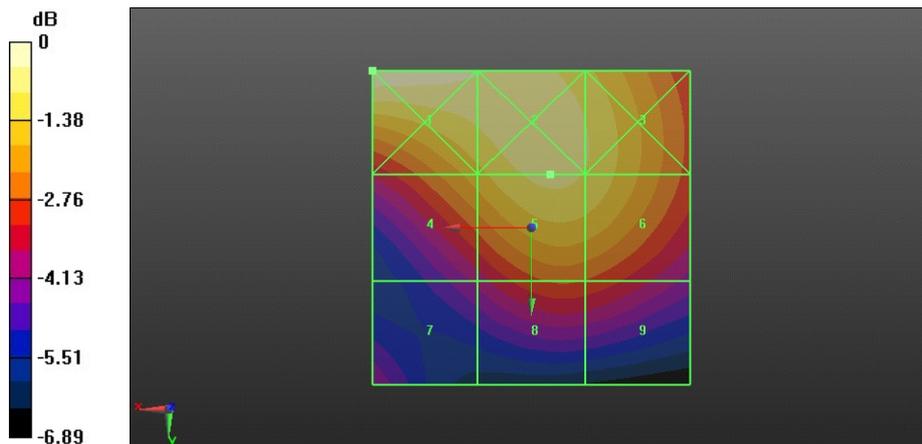
Grid 1 M4 <b>0.097 A/m</b>	Grid 2 M4 <b>0.092 A/m</b>	Grid 3 M4 <b>0.087 A/m</b>
Grid 4 M4 <b>0.081 A/m</b>	Grid 5 M4 <b>0.088 A/m</b>	Grid 6 M4 <b>0.087 A/m</b>
Grid 7 M4 <b>0.061 A/m</b>	Grid 8 M4 <b>0.071 A/m</b>	Grid 9 M4 <b>0.070 A/m</b>

**Cursor:**

Total = 0.09661 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.09661 A/m = -20.30 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-UMTS Band V 4233CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 65.66 V/m; Power Drift = -0.05 dB

PMF = 1.040 is applied.

E-field emissions = 54.12 V/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled E-field

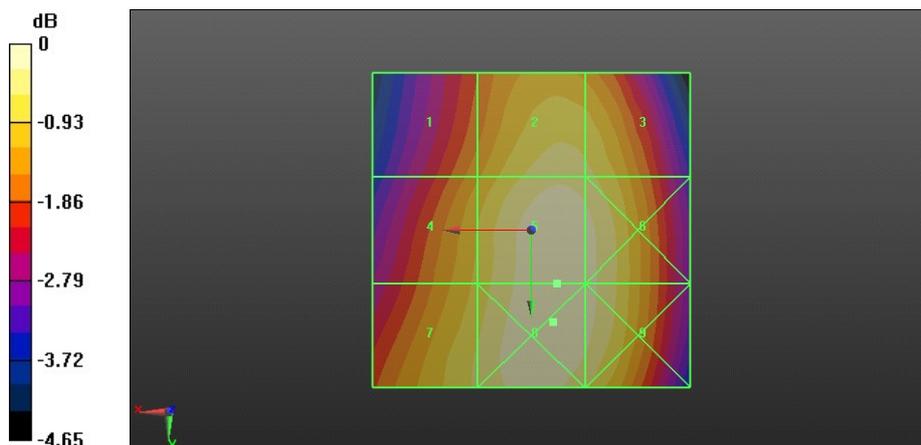
Grid 1 M4 46.68 V/m	Grid 2 M4 51.92 V/m	Grid 3 M4 51.19 V/m
Grid 4 M4 49.27 V/m	Grid 5 M4 54.12 V/m	Grid 6 M4 53.19 V/m
Grid 7 M4 50.87 V/m	Grid 8 M4 54.23 V/m	Grid 9 M4 53.19 V/m

**Cursor:**

Total = 54.23 V/m

E Category: M4

Location: -3.5, 14.5, 8.7 mm



0 dB = 54.23 V/m = 34.69 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-UMTS Band V 4182CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SAR1**

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 64.17 V/m; Power Drift = -0.03 dB

PMF = 1.040 is applied.

E-field emissions = 53.42 V/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled E-field

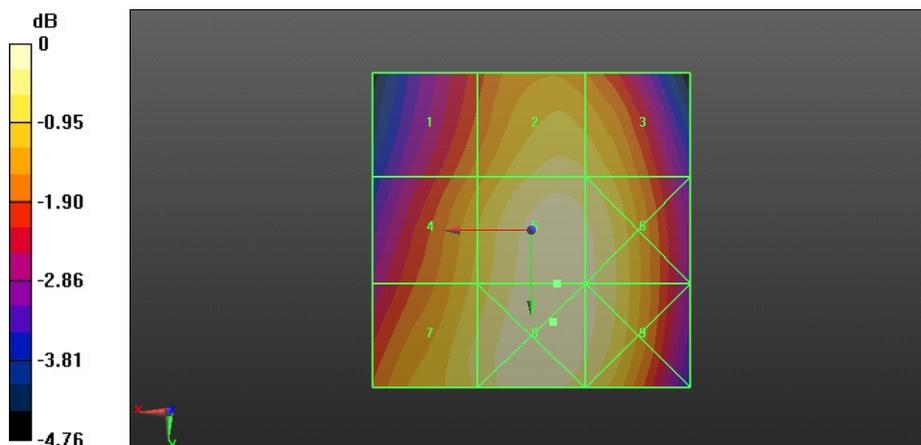
Grid 1 M4 45.69 V/m	Grid 2 M4 50.85 V/m	Grid 3 M4 50.16 V/m
Grid 4 M4 48.78 V/m	Grid 5 M4 53.42 V/m	Grid 6 M4 52.51 V/m
Grid 7 M4 50.50 V/m	Grid 8 M4 53.65 V/m	Grid 9 M4 52.53 V/m

**Cursor:**

Total = 53.65 V/m

E Category: M4

Location: -3.5, 14.5, 8.7 mm



0 dB = 53.65 V/m = 34.59 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-UMTS Band V 4132CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SAR1**

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 59.98 V/m; Power Drift = -0.03 dB

PMF = 1.040 is applied.

E-field emissions = 49.80 V/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled E-field

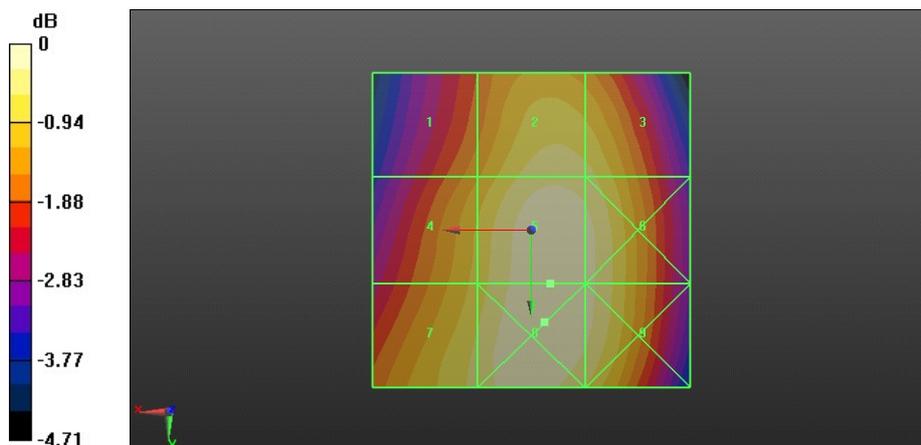
Grid 1 M4 43.02 V/m	Grid 2 M4 47.75 V/m	Grid 3 M4 47.14 V/m
Grid 4 M4 45.55 V/m	Grid 5 M4 49.80 V/m	Grid 6 M4 48.91 V/m
Grid 7 M4 47.09 V/m	Grid 8 M4 49.96 V/m	Grid 9 M4 48.91 V/m

**Cursor:**

Total = 49.96 V/m

E Category: M4

Location: -2, 14.5, 8.7 mm



0 dB = 49.96 V/m = 33.97 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_ER3DV6\_H883G-UMTS Band V 4233CH with battery 2#**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SAR1**

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 64.63 V/m; Power Drift = -0.14 dB

PMF = 1.040 is applied.

E-field emissions = 53.08 V/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled E-field

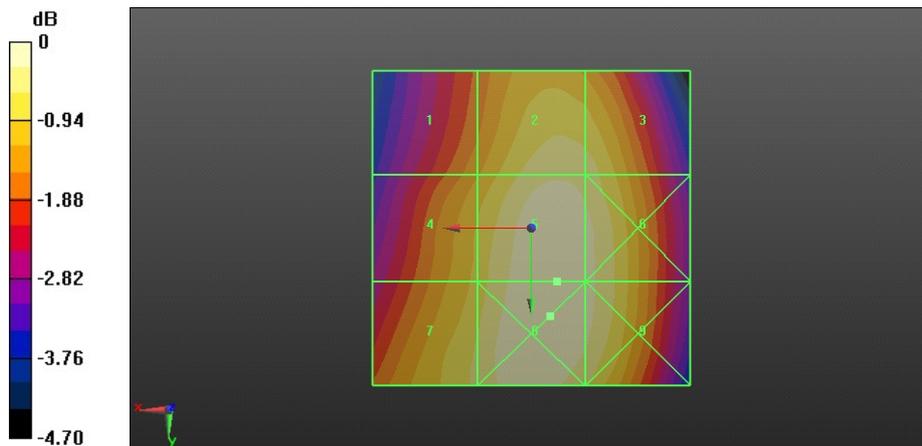
Grid 1 M4 45.86 V/m	Grid 2 M4 51.02 V/m	Grid 3 M4 50.52 V/m
Grid 4 M4 48.44 V/m	Grid 5 M4 53.08 V/m	Grid 6 M4 52.05 V/m
Grid 7 M4 50.00 V/m	Grid 8 M4 53.19 V/m	Grid 9 M4 52.06 V/m

**Cursor:**

Total = 53.19 V/m

E Category: M4

Location: -3, 14, 8.7 mm



0 dB = 53.19 V/m = 34.52 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-UMTS Band V-4233CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1;Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz;Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06500 A/m; Power Drift = -0.09 dB

PMF = 1.020 is applied.

H-field emissions = 0.08514 A/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled H-field

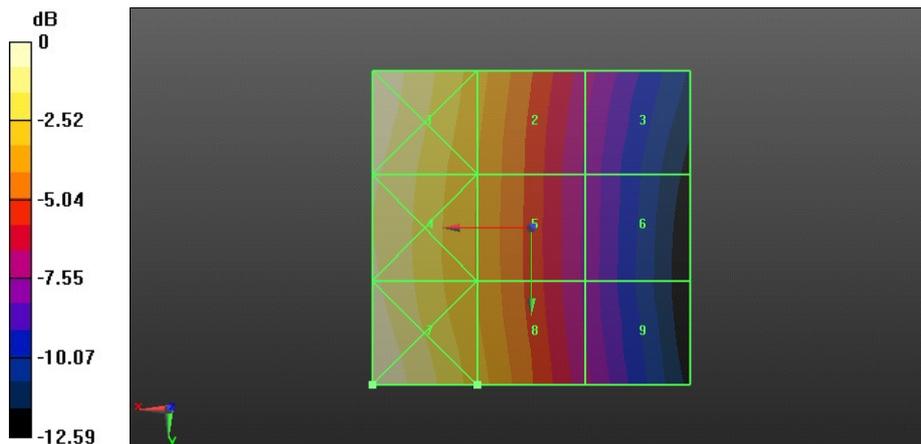
<b>Grid 1 M4</b> <b>0.118 A/m</b>	<b>Grid 2 M4</b> <b>0.085 A/m</b>	<b>Grid 3 M4</b> <b>0.053 A/m</b>
<b>Grid 4 M4</b> <b>0.110 A/m</b>	<b>Grid 5 M4</b> <b>0.081 A/m</b>	<b>Grid 6 M4</b> <b>0.049 A/m</b>
<b>Grid 7 M4</b> <b>0.119 A/m</b>	<b>Grid 8 M4</b> <b>0.085 A/m</b>	<b>Grid 9 M4</b> <b>0.052 A/m</b>

**Cursor:**

Total = 0.1194 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1194 A/m = -18.46 dB A/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-UMTS Band V-4182CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1; Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06400 A/m; Power Drift = -0.04 dB

PMF = 1.020 is applied.

H-field emissions = 0.08393 A/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled H-field

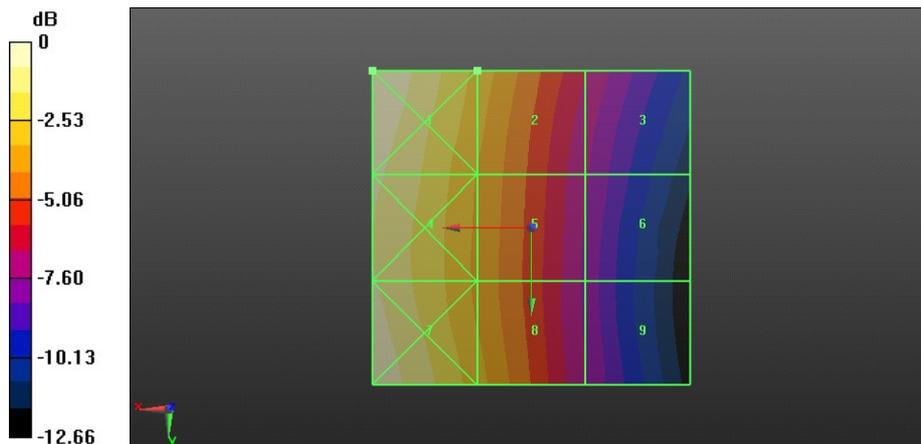
<b>Grid 1 M4</b> <b>0.115 A/m</b>	<b>Grid 2 M4</b> <b>0.084 A/m</b>	<b>Grid 3 M4</b> <b>0.053 A/m</b>
<b>Grid 4 M4</b> <b>0.107 A/m</b>	<b>Grid 5 M4</b> <b>0.078 A/m</b>	<b>Grid 6 M4</b> <b>0.049 A/m</b>
<b>Grid 7 M4</b> <b>0.115 A/m</b>	<b>Grid 8 M4</b> <b>0.082 A/m</b>	<b>Grid 9 M4</b> <b>0.048 A/m</b>

**Cursor:**

Total = 0.1154 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.1154 A/m = -18.76 dB A/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-UMTS Band V-4132CH**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Ascend W1; Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06100 A/m; Power Drift = -0.01 dB

PMF = 1.020 is applied.

H-field emissions = 0.07888 A/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled H-field

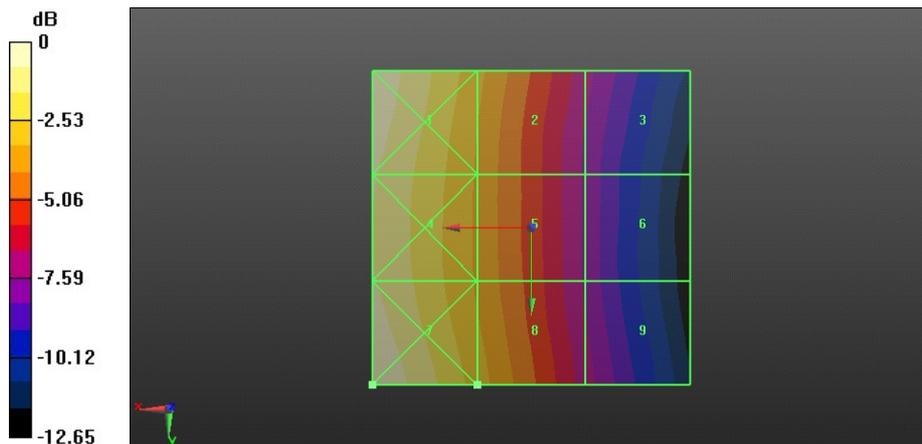
<b>Grid 1 M4</b> <b>0.108 A/m</b>	<b>Grid 2 M4</b> <b>0.077 A/m</b>	<b>Grid 3 M4</b> <b>0.048 A/m</b>
<b>Grid 4 M4</b> <b>0.101 A/m</b>	<b>Grid 5 M4</b> <b>0.074 A/m</b>	<b>Grid 6 M4</b> <b>0.045 A/m</b>
<b>Grid 7 M4</b> <b>0.110 A/m</b>	<b>Grid 8 M4</b> <b>0.079 A/m</b>	<b>Grid 9 M4</b> <b>0.048 A/m</b>

**Cursor:**

Total = 0.1102 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1102 A/m = -19.16 dB A/m

Test Laboratory: HUAWEI SAR/HAC Lab

**HAC\_H3DV6\_H883G-UMTS Band V-4233CH with battery 2#**

**DUT: H883G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Cteqpf 'Y 3=Serial: SAR1**

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz; Duty Cycle: 1:1

Medium parameters used:  $\sigma = 0$  mho/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

**Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm**

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06500 A/m; Power Drift = -0.17 dB

PMF = 1.020 is applied.

H-field emissions = 0.08438 A/m

**Near-field category: M4 (AWF 0 dB)**

PMF scaled H-field

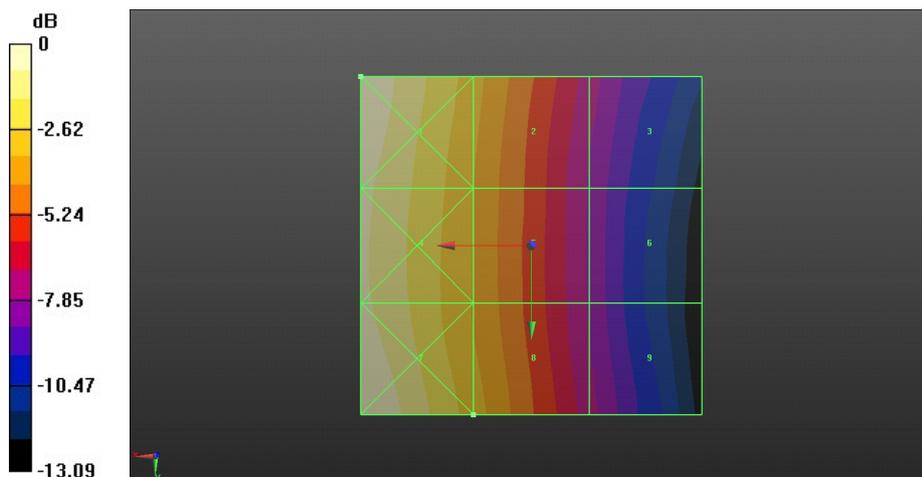
<b>Grid 1 M4</b> <b>0.120 A/m</b>	<b>Grid 2 M4</b> <b>0.084 A/m</b>	<b>Grid 3 M4</b> <b>0.051 A/m</b>
<b>Grid 4 M4</b> <b>0.112 A/m</b>	<b>Grid 5 M4</b> <b>0.080 A/m</b>	<b>Grid 6 M4</b> <b>0.048 A/m</b>
<b>Grid 7 M4</b> <b>0.120 A/m</b>	<b>Grid 8 M4</b> <b>0.084 A/m</b>	<b>Grid 9 M4</b> <b>0.051 A/m</b>

**Cursor:**

Total = 0.1199 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.1199 A/m = -18.42 dBA/m